

Single Zener diodes in a SOD123F package Rev. 3 — 7 December 2010

Product data sheet

Unit V

mW

mW

830

1. **Product profile**

1.1 General description

General-purpose Zener diodes in a SOD123F small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features and benefits

- Total power dissipation: ≤ 830 mW
- Wide working voltage range: nominal 2.4 V to 75 V (E24 range)
- Small plastic package suitable for surface-mounted design

1.3 Applications

General regulation functions

1.4 Quick reference data

Table 1.	Quick reference data				
Symbol	Parameter	Conditions	Min	Тур	Max
V _F	forward voltage	I _F = 10 mA	<u>[1]</u> _	-	0.9
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[2] _	-	375

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

Pinning information 2.

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	
2	anode	1 2	1 <u> </u>

[1] The marking bar indicates the cathode.



- Low differential resistance
- AEC-Q101 qualified

[3] _

-

Single Zener diodes in a SOD123F package

3. Ordering information

Table 3. Ordering	information					
Type number	Package					
	Name	Description	Version			
BZT52H-B2V4 to BZT52H-C75 ^[1]	-	plastic surface-mounted package; 2 leads	SOD123F			

[1] The series consists of 74 types with nominal working voltages from 2.4 V to 75 V.

4. Marking

Table 4. Mark	ing codes						
Type number	Marking code	Type number	Marking code	Type number	Marking code	Type number	Marking code
BZT52H-B2V4	DC	BZT52H-B15	DX	BZT52H-C2V4	B3	BZT52H-C15	BN
BZT52H-B2V7	DD	BZT52H-B16	DY	BZT52H-C2V7	B4	BZT52H-C16	BP
BZT52H-B3V0	DE	BZT52H-B18	DZ	BZT52H-C3V0	B5	BZT52H-C18	BQ
BZT52H-B3V3	DF	BZT52H-B20	E1	BZT52H-C3V3	B6	BZT52H-C20	BR
BZT52H-B3V6	DG	BZT52H-B22	E2	BZT52H-C3V6	B7	BZT52H-C22	BS
BZT52H-B3V9	DH	BZT52H-B24	E3	BZT52H-C3V9	B8	BZT52H-C24	BT
BZT52H-B4V3	DJ	BZT52H-B27	E4	BZT52H-C4V3	B9	BZT52H-C27	BU
BZT52H-B4V7	DK	BZT52H-B30	E5	BZT52H-C4V7	BA	BZT52H-C30	BV
BZT52H-B5V1	DL	BZT52H-B33	E6	BZT52H-C5V1	BB	BZT52H-C33	BW
BZT52H-B5V6	DM	BZT52H-B36	E7	BZT52H-C5V6	BC	BZT52H-C36	BX
BZT52H-B6V2	DN	BZT52H-B39	E8	BZT52H-C6V2	BD	BZT52H-C39	BY
BZT52H-B6V8	DP	BZT52H-B43	E9	BZT52H-C6V8	BE	BZT52H-C43	BZ
BZT52H-B7V5	DQ	BZT52H-B47	EA	BZT52H-C7V5	BF	BZT52H-C47	C1
BZT52H-B8V2	DR	BZT52H-B51	EB	BZT52H-C8V2	BG	BZT52H-C51	C2
BZT52H-B9V1	DS	BZT52H-B56	EC	BZT52H-C9V1	BH	BZT52H-C56	C3
BZT52H-B10	DT	BZT52H-B62	ED	BZT52H-C10	BJ	BZT52H-C62	C4
BZT52H-B11	DU	BZT52H-B68	EE	BZT52H-C11	BK	BZT52H-C68	C5
BZT52H-B12	DV	BZT52H-B75	EF	BZT52H-C12	BL	BZT52H-C75	C6
BZT52H-B13	DW	-	-	BZT52H-C13	BM	-	-

Single Zener diodes in a SOD123F package

5. Limiting values

Table 5. In accorda	Limiting values ance with the Absolute Maxir	num Rating System (IE	C 60134).		
Symbol	Parameter	Conditions	Min	Мах	Unit
I _F	forward current		-	250	mA
I _{ZSM}	non-repetitive peak reverse current		-	see <u>Table 8,9</u> and <u>10</u>	
P _{ZSM}	non-repetitive peak reverse power dissipation		<u>[1]</u> _	40	W
P _{tot}	total power dissipation	$T_{amb} \leq 25 \ ^{\circ}C$	[2] -	375	mW
			<u>[3]</u> _	830	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C
[1] + _ 10	0 us: square ways: $T_{\rm r} = 25 ^{\circ}{\rm C}$ r	vrier to ourge			

[1] $t_p = 100 \ \mu s$; square wave; $T_j = 25 \ ^\circ C$ prior to surge.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics										
Symbol	Parameter	Conditions	Min	Тур	Max	Unit					
R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> _	-	330	K/W					
	junction to ambient		[2] _	-	150	K/W					
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[3]</u>	-	70	K/W					

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

[3] Soldering point of cathode tab.

Single Zener diodes in a SOD123F package

7. Characteristics

Table 7.	Characteristics	
$T_i = 25 \ ^{\circ}C$	unless otherwise specified.	

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
V _F	forward voltage	I _F = 10 mA	<u>[1]</u> _	-	0.9	V				

[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

Table 8. Characteristics per type; BZT52H-B2V4 to BZT52H-C24

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

BZT52H Sel -xxx		Worki voltag V _Z (V) I _Z = 5	je ;	Maximum resistance	differential r _{dif} (Ω)	Revers current	e t I _R (μΑ)	Tempe coeffic S _Z (m) I _Z = 5 (//K);	Diode capacitance C _d (pF) ^[1]	Non-repetitive peak reverse current I _{ZSM} (A) ^[2]
		Min	Max	I _Z = 1 mA	I _Z = 5 mA	Max	V _R (V)	Min	Max	Max	Max
2V4	В	2.35	2.45	400	85	50	1	-3.5	0.0	450	6.0
	С	2.2	2.6								
2V7	В	2.65	2.75	500	83	20	1	-3.5	0.0	450	6.0
	С	2.5	2.9								
3V0	В	2.94	3.06	500	95	10	1	-3.5	0.0	450	6.0
	С	2.8	3.2								
3V3	В	3.23	3.37	500	95	5	1	-3.5	0.0	450	6.0
	С	3.1	3.5								
3V6	В	3.53	3.67	500	95	5	1	-3.5	0.0	450	6.0
	С	3.4	3.8								
3V9	В	3.82	3.98	500	95	3	1	-3.5	0.0	450	6.0
	С	3.7	4.1								
4V3	В	4.21	4.39	500	95	3	1	-3.5	0.0	450	6.0
	С	4.0	4.6								
4V7	В	4.61	4.79	500	78	3	2	-3.5	0.2	300	6.0
	С	4.4	5.0								
5V1	В	5.0	5.2	480	60	2	2	-2.7	1.2	300	6.0
	С	4.8	5.4								
5V6	В	5.49	5.71	400	40	1	2	-2.0	2.5	300	6.0
	С	5.2	6.0								
6V2	В	6.08	6.32	150	10	3	4	0.4	3.7	200	6.0
	С	5.8	6.6								
6V8	В	6.66	6.94	80	8	2	4	1.2	4.5	200	6.0
	С	6.4	7.2								
7V5	В	7.35	7.65	80	10	1	5	2.5	5.3	150	4.0
	С	7.0	7.9								
3V2	В	8.04	8.36	80	10	0.7	5	3.2	6.2	150	4.0
	С	7.7	8.7								

Single Zener diodes in a SOD123F package

BZT52H Sel -xxx		el Working voltage V _Z (V); I _Z = 5 mA			Maximum differential resistance r _{dif} (Ω)		se t I _R (μΑ)	Tempo coeffi S _Z (m ¹ I _Z = 5	V/K);	Diode capacitance C _d (pF) ^[1]	Non-repetitive peak reverse current I _{ZSM} (A) ^[2]
		Min	Max	I _Z = 1 mA	I _Z = 5 mA	Max	V _R (V)	Min	Max	Max	Max
9V1	В	8.92	9.28	100	10	0.5	6	3.8	7.0	150	3.0
	С	8.5	9.6								
10	В	9.8	10.2	70	10	0.2	7	4.5	8.0	90	3.0
	С	9.4	10.6								
11	В	10.8	11.2	70	10	0.1	8	5.4	9.0	85	2.5
	С	10.4	11.6								
12	В	11.8	12.2	90	10	0.1	8	6.0	10.0	85	2.5
	С	11.4	12.7								
13	В	12.7	13.3	110	10	0.1	8	7.0	11.0	80	2.5
	С	12.4	14.1								
15	В	14.7	4.7 15.3 110	110	15	0.05	10.5	9.2	13.0	75	2.0
	С	13.8	15.6								
16	В	15.7	16.3	170	20	0.05	11.2	10.4	14.0	75	1.5
	С	15.3	17.1								
18	В	17.6	18.4	170	20	0.05	12.6	12.4	16.0	70	1.5
	С	16.8	19.1								
20	В	19.6	20.4	220	20	0.05	14	14.4	18.0	60	1.5
	С	18.8	21.2								
22	В	21.6	22.4	220	25	0.05	15.4	16.4	20.0	60	1.25
	С	20.8	23.3								
24	В	23.5	24.5	220	30	0.05	16.8	18.4	22.0	55	1.25
	С	22.8	25.6								

Table 8. Characteristics per type; BZT52H-B2V4 to BZT52H-C24 ...continued

[1] $f = 1 \text{ MHz}; V_R = 0 \text{ V}.$

[2] $t_p = 100 \ \mu s; T_{amb} = 25 \ ^{\circ}C.$

Single Zener diodes in a SOD123F package

BZT52H Sel -xxx		el Working voltage V _Z (V); I _Z = 2 mA		Maximum differential resistance r _{dif} (Ω)		current I _R (μΑ)		Temperature coefficient S _Z (mV/K); I _Z = 5 mA		Diode capacitance C _d (pF) <mark>[1]</mark>	Non-repetitive peak reverse current I _{ZSM} (A) ^[2]
		Min	Мах	I _Z = 1 mA	I _Z = 5 mA	Мах	V _R (V)	Min	Max	Max	Max
27	В	26.5	27.5	250	40	0.05	18.9	21.4	25.3	50	1.0
	С	25.1	28.9								
30	В	29.4	30.6	250	40	0.05	21	24.4	29.4	50	1.0
	С	28.0	32.0								
33	В	32.3	33.7	250	40	0.05	23.1	27.4	33.4	45	0.9
	С	31.0	35.0								
36	В	35.3	36.7	250	60	0.05	25.2	30.4	37.4	45	0.8
	С	34.0	38.0								
39	В	38.2	39.8	300	75	0.05	27.3	33.4	33.4 41.2	45	0.7
	С	37.0	41.0								
43	В	42.1	43.9	325	80	0.05	30.1	37.6	46.6	40	0.6
	С	40.0	46.0								
47	В	46.1	47.9	325	90	0.05	32.9	42.0	51.8	40	0.5
	С	44.0	50.0								
51	В	50.0	52.0	350	100	0.05	35.7	46.6	46.6 57.2	40	0.4
	С	48.0	54.0								

Table 9.Characteristics per type; BZT52H-B27 to BZT52H-C51 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

[1] $f = 1 \text{ MHz}; V_R = 0 \text{ V}.$

[2] $t_p = 100 \ \mu s; T_{amb} = 25 \ ^{\circ}C.$

Table 10. Characteristics per type; BZT52H-B56 to BZT52H-C75

 $T_i = 25 \ ^{\circ}C$ unless otherwise specified.

BZT52H Sel -xxx		Working voltage V _Z (V); I _Z = 2 mA		Maximum differential resistance r _{dif} (Ω)			Reverse current I _R (μΑ)		erature cient //K); mA	Diode capacitance C _d (pF) ^[1]	Non-repetitive peak reverse current I _{ZSM} (A) ^[2]
		Min	Max	I _Z = 0.5 mA	I _Z = 2 mA	Max	V _R (V)	Min	Max	Max	Мах
56	В	54.9	57.1	375	120	0.05	39.2	52.2	63.8	40	0.3
	С	52.0	60.0								
62	В	60.8	63.2	400	140	40 0.05 4	43.4	58.8	71.6	35	0.3
	С	58.0	66.0								
68	В	66.6	69.4	400	160	0.05	47.6	65.6	79.8	35	0.25
	С	64.0	72.0								
75	В	73.5	76.5	400 175	0.05	52.5	73.4	3.4 88.6	35	0.20	
	С	70.0	79.0								

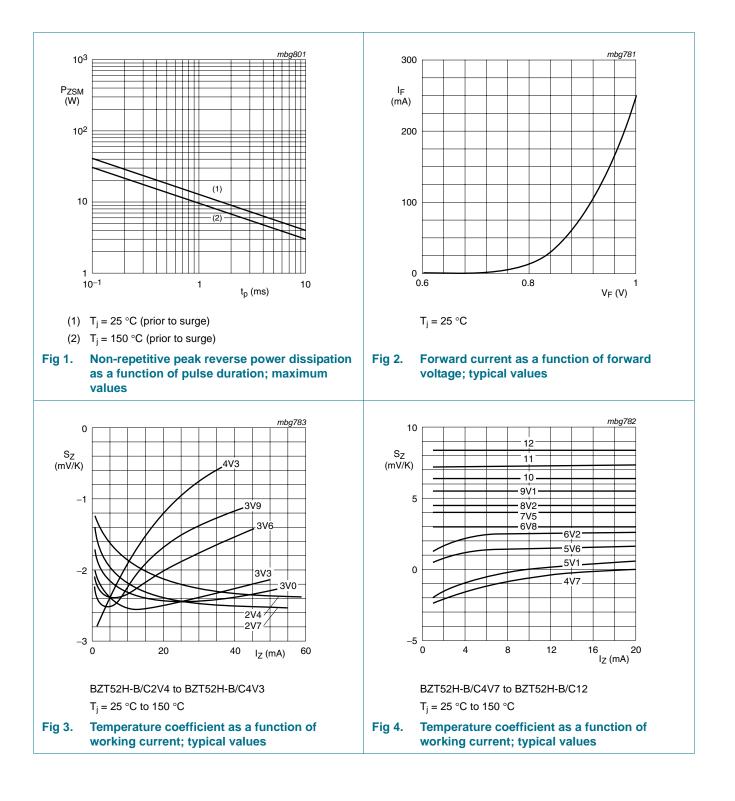
[1] $f = 1 \text{ MHz}; V_R = 0 \text{ V}.$

[2] $t_p = 100 \ \mu s; T_{amb} = 25 \ ^{\circ}C.$

NXP Semiconductors

BZT52H series

Single Zener diodes in a SOD123F package



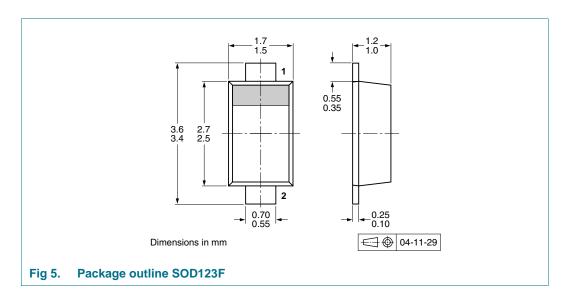
Single Zener diodes in a SOD123F package

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 11. Packing methods

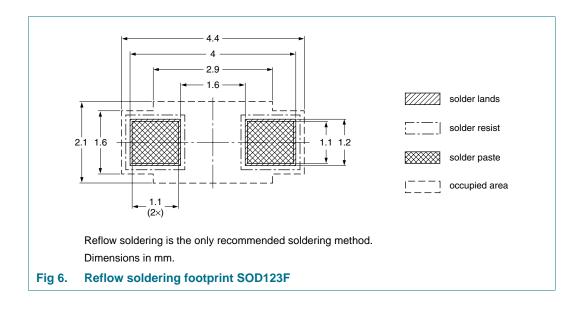
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
BZT52H-B2V4 to BZT52H-C75	SOD123F	4 mm pitch, 8 mm tape and reel	-115	-135

[1] For further information and the availability of packing methods, see Section 14.

Single Zener diodes in a SOD123F package

11. Soldering



Single Zener diodes in a SOD123F package

12. Revision history

Table 12. Revision h	nistory					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BZT52H_SER v.3	20101207	Product data sheet	-	BZT52H_SER v.2		
Modifications:	Added selection B.					
	 <u>Section 1.2 "Features and benefits"</u>: amended. 					
	 <u>Table 2 "Pinning"</u>: graphic symbol updated. 					
	 <u>Section 8 "Test information"</u>: added. 					
	 <u>Section 13 "Legal information"</u>: updated. 					
BZT52H_SER v.2	20091115	Product data sheet	-	BZT52H_SER v.1		
BZT52H_SER v.1	20051222	Product data sheet	-	-		

Single Zener diodes in a SOD123F package

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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11 of 13

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Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

14. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

12 of 13

Single Zener diodes in a SOD123F package

15. Contents

1	Product profile 1
1.1	General description 1
1.2	Features and benefits 1
1.3	Applications 1
1.4	Quick reference data 1
2	Pinning information 1
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 3
7	Characteristics 4
8	Test information 8
8.1	Quality information 8
9	Package outline 8
10	Packing information 8
11	Soldering 9
12	Revision history 10
13	Legal information 11
13.1	Data sheet status 11
13.2	Definitions 11
13.3	Disclaimers
13.4	Trademarks 12
14	Contact information 12
15	Contents 13

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 BZT52H-B16,115

 BZT52H-B18,115
 BZT52H-B20,115
 BZT52H-B22,115
 BZT52H-B24,115
 BZT52H-B27,115
 BZT52H-B2V4,115

 BZT52H-B2V7,115
 BZT52H-B30,115
 BZT52H-B33,115
 BZT52H-B39,115
 BZT52H-B3V0,115

 BZT52H-B3V3,115
 BZT52H-B3V6,115
 BZT52H-B30,115
 BZT52H-B30,115
 BZT52H-B4V7,115
 BZT52H-B3V0,115

 BZT52H-B4V7,115
 BZT52H-B51,115
 BZT52H-B56,115
 BZT52H-B5V1,115
 BZT52H-B6V2,115
 BZT52H-B6V2,115

 BZT52H-B68,115
 BZT52H-B6V2,115
 BZT52H-B6V8,115
 BZT52H-B7V5,115
 BZT52H-B8V2,115

 BZT52H-B9V1,115
 BZT52H-C10,115
 BZT52H-C11,115
 BZT52H-C12,115
 BZT52H-C15,115

 BZT52H-C16,115
 BZT52H-C10,115
 BZT52H-C20,115
 BZT52H-C24,115
 BZT52H-C27,115

 BZT52H-C2V4,115
 BZT52H-C18,115
 BZT52H-C20,115
 BZT52H-C33,115
 BZT52H-C30,115
 BZT52H-C30,115

 BZT52H-C2V4,115
 BZT52H-C2V7,115
 BZT52H-C30,115
 BZT52H-C30,115
 BZT52H-C30,115
 BZT52H-C44,115
 BZT52H-C47,115